

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

FEB 20 2002

(use as many sheets as necessary)

Sheet

1

of

2

Complete if Known

Application Number	Not Yet Assigned
Filing Date	11-09-2001
First Named Inventor	Brian S. Doyle, et al.
Group Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	42390P5768D

## OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published
De		G.A. HISHMEH & L. CARTZ, F. DESAGE, C. TEMPLIER, & J.C. DESOYER, R.C. BIRTCHER; Rare Gas Bubbles in Muscovite Mica Implanted with Xenon and Krypton; J. Mater. Res., Vol. 9 No. 12, December 1994, pp. 3095-3107.
		REIJI YAMADA, STEVEN J. ZINKLE, G. PHILIP PELLIS; Microstructure of Al <sub>2</sub> O <sub>3</sub> and MgAl <sub>2</sub> O <sub>4</sub> Preimplanted with H, He, C and Irradiated with Ar <sup>+</sup> ions*; Elsevier Science B.V.; Journal of Nuclear Materials 209 (1994); pp. 191-203.
		E.D. SPECHT, D.A. WALKO, & S.J. ZINKLE; Density Reduction: A Mechanism for Amorphization at High Ion Doses; Mat.Res.Soc.Symp.Proc. Vol. 316; 1994 Materials Research Society, pp. 241-246.
		V. JESCHKE & G.H. FRISCHAT; Gas Bubbles in Glass Melts Under Microgravity. Part 2. Helium Diffusion; Physics and Chemistry of Glasses Vol. 28, No. 5, October 1987; pp. 177-182.
		N. MORIYA, Y. SHACHAM-DIAMOND, R. KALISH; Modification Effects in Ion-Implanted SiO <sub>2</sub> Spin-on-Glass; J. Electrochem. Soc., Vol. 140, No. 5, May 1993, The Electrochemical Society, Inc., pp. 1442-1450.
		R. SIEGELE, G.C. WEATHERLY & H.K. HAUGEN, D.J. LOCKWOOD, L.M. HOWE; Helium Bubbles in Silicon: Structure and Optical Properties; Appl. Phys. Lett. 66 (11) 13 March 1995, 1995 American Institute of Physics, pp. 1319-1321.
		D. BISERO, F. CORNI, C. NOBILI, R. TONINI, & G. OTTAVIANI, C. MAZZOLENI, L. PAVESI; Visible Photoluminescence from He-implanted Silicon; Appl. Phys. Lett. 67 (23) 4 December 1995; American Institute of Physics; pp. 3447-3449.
		A. VAN VEEN, C.C. GRIFFIOEN, & J.H. EVANS; Helium-Induced Porous Layer Formation in Silicon; Material Research Society, Mat. Res. Soc. Symp. Proc. Vol. 107; pp. 449-454.
		V. RAINERI, G. FALLICA, S. LIBERTINO; Lifetime Control in Silicon Devices by Voids Induced by He Ion Implantation; J. Appl. Phys. 79 (12). 15 June 1996, American Institute of Physics; pp. 9012-9016.
		D.M. FOLLSTAEDT, S.M. MYERS, S.R. LEE, J.L. RENO, R.L. DAWSON & J. HAN; Interaction of Cavities and Dislocations in Semiconductors; Mat. Res. Soc. Symp. Proc. Vol. 438, 1997 Materials Research Society, pp. 229-234.
De		J.W. MEDERNACH, T.A. HILL, S.M. MYERS, AND T.J. HEADLEY; Microstructural Properties of Helium Implanted Void Layers in Silicon as Related to Front-Side Gettering; J. Electrochem. Vol. 143, No. 2, February 1996, The Electrochemical Society, Inc., pp. 725-735.

Examiner  
Signature

Dmug fushu

Date

Considered

3/03

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.

Under the Paperwork Reduction Act of 1995, this collection of information does not have a burden estimate, a review of existing collection of information, a statement of the necessity of the collection of information, and a statement of the estimated burden for the collection of information, because this collection of information is not subject to the requirements of the act. This collection of information is not a collection of information for the purposes of the act. It is a collection of information for the purposes of the act.

U.S. Patent and Trademark Office U.S. DEPARTMENT OF COMMERCE  
No persons are required to respond to a collection of information unless it contains a valid OMB

Substitute for form 1449B/PTO

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

*(use as many sheets as necessary)*

2003 年 12 月

2

of

2

**Complete if Known**

Application Number

Not Yet Assigned

Filing Date

11-09-2001

**First Named Inventor**

Brian S. Doyle, et al.

## Group Art Unit

Not Yet Assigned

**Examiner Name**

Not Yet Assigned

Attorney Docket Number

42390P5768D

### OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

[illegible]

Examiner  
Signature

Date \_\_\_\_\_

Considered

3/05

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

**Burden Hour Statement:** This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. **DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO:** Assistant Commissioner for Patents, Washington, DC 20231.